30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.040\Omega$; $I_D = -6.7A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



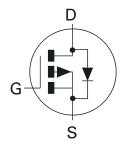
SO8

FEATURES

- Low on-resistance
- · Fast switching speed
- · Low threshold
- · Low gate drive
- Low profile SOIC package

APPLICATIONS

- Disconnect switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A16N8TA	7″	12mm	500 units
ZXMP3A16N8TC	13"	12mm	2500 units

DEVICE MARKING

 ZXMP 3A16

PINOUT



Top View



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current V_{GS} =-10V; T_A =25°C (b) V_{GS} =-10V; T_A =70°C (b) V_{GS} =-10V; T_A =25°C (a)	I _D	-6.7 -5.4 -5.6	А
Pulsed Drain Current (c)	I _{DM}	-26	А
Continuous Source Current (Body Diode) (b)	I _S	-3.2	А
Pulsed Source Current (Body Diode) (c)	I _{SM}	-26	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	1.9 15.2	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	2.8 22.4	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT					
Junction to Ambient (a)	$R_{\theta JA}$	65	°C/W					
Junction to Ambient (b)	$R_{\theta JA}$	45	°C/W					

NOTES

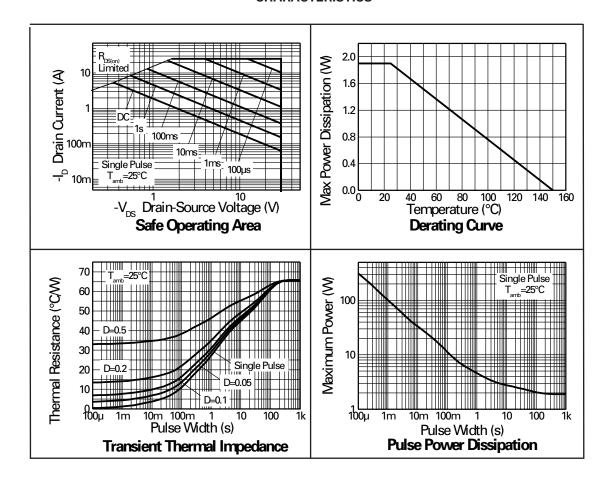
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions



⁽b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

⁽c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width $10\,\mu s$ - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

CHARACTERISTICS





ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

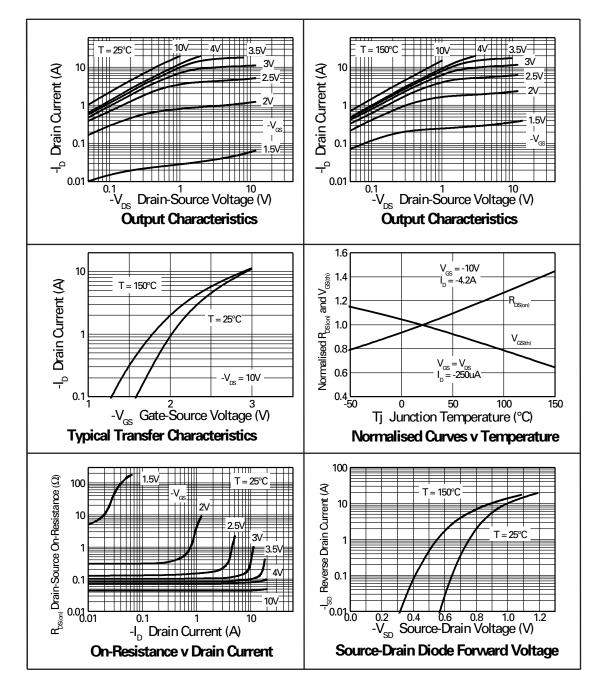
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS		
STATIC								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V		
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μΑ	V _{DS} =-30V, V _{GS} =0V		
Gate-Body Leakage	I _{GSS}			100	nA	V_{GS} = $\pm 20V$, V_{DS} = $0V$		
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	$I_D = -250 \mu A, V_{DS} = V_{GS}$		
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.040 0.070	$\Omega \Omega$	V _{GS} =-10V, I _D =-4.2A V _{GS} =-4.5V, I _D =-3.4A		
Forward Transconductance (1)(3)	g _{fs}		9.2		S	V _{DS} =-15V,I _D =-4.2A		
DYNAMIC (3)		'	•	•				
Input Capacitance	C _{iss}		1022		pF			
Output Capacitance	Coss		267		pF	V _{DS} =-15 V, V _{GS} =0V, f=1MHz		
Reverse Transfer Capacitance	C _{rss}		229		pF	11-1141112		
SWITCHING(2) (3)								
Turn-On Delay Time	t _{d(on)}		3.8		ns			
Rise Time	t _r		6.5		ns	V _{DD} =-15V, I _D =-1A		
Turn-Off Delay Time	t _{d(off)}		37.1		ns	$R_G=6.0\Omega$, $V_{GS}=-10V$		
Fall Time	t _f		21.4		ns			
Gate Charge	Q_g		17.2		nC	V _{DS} =-15V,V _{GS} =-5V, I _D =-4.2A		
Total Gate Charge	Qg		29.6		nC	V _{DS} =-15V,V _{GS} =-10V, I _D =-4.2A		
Gate-Source Charge	Q _{gs}		2.8		nC			
Gate-Drain Charge	Q _{gd}		8.6		nC			
SOURCE-DRAIN DIODE						,		
Diode Forward Voltage (1)	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-3.6A, V _{GS} =0V		
Reverse Recovery Time (3)	t _{rr}		21.7		ns	T _J =25°C, I _F =-2A, di/dt= 100A/μs		
Reverse Recovery Charge (3)	Q _{rr}		16.1		nC			

NOTES

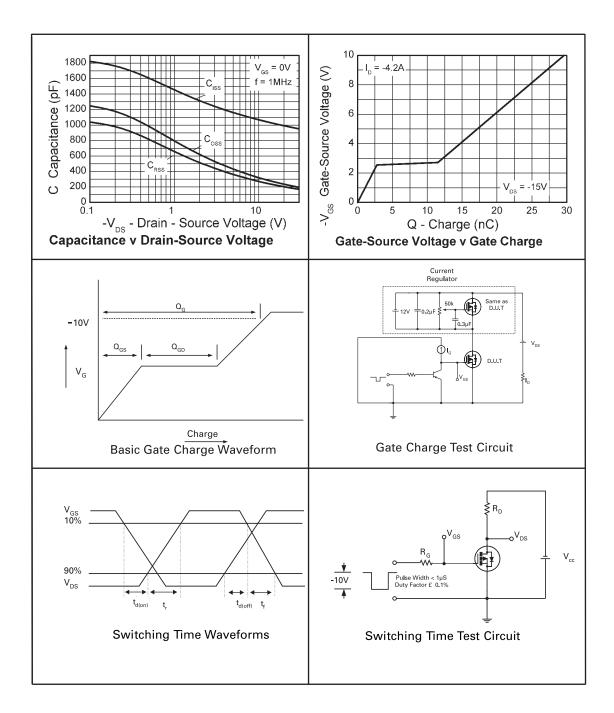
- (1) Measured under pulsed conditions. Width ${\leq}300\mu s.$ Duty cycle ${\leq}\,2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



CHARACTERISTICS









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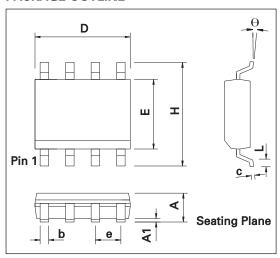
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

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PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES APPROX IN MILLIMETERS

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DINA	Millimeters		Inches	
	Min	Max	Min	Max	DIM	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069	е	1.27 BSC		0.050 BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	С	0.19	0.25	0.008	0.010
Н	5.80	6.20	0.228	0.244	θ	0°	8°	0°	8°
Е	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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